

## N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>(BR)DSS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)			
75	0.0062 at $V_{GS}$ = 10 V	90 <sup>d</sup>	75			

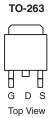
### **FEATURES**

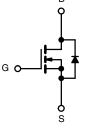
- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>q</sub> and UIS Tested

### **APPLICATIONS**

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- Power Supply - Secondary Synchronous Rectification
- Industrial





Ordering Information: SUM90N08-6m2P-E3 (Lead (Pb)-free)

N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_{C} = 25 \text{ °C}$ , unless otherwise noted					
Parameter	-	Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	75	v	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current ( $T_1 = 175 ^{\circ}C$ )	T <sub>C</sub> = 25 °C	L_	90 <sup>d</sup>		
Continuous Drain Current $(1j = 175 \text{ C})$	T <sub>C</sub> = 70 °C	I <sub>D</sub>	90 <sup>d</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	240	A	
Avalanche Current		I <sub>AS</sub>	50	-	
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
	T <sub>C</sub> = 25 °C	D	272 <sup>b</sup>		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	– P <sub>D</sub> –	3.75	W	
Operating Junction and Storage Temperature Ra	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.55			

Notes:

a. Duty cycle  $\leq$  1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

d. Package limited.



# SUM90N08-6m2P

## Vishay Siliconix



Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 V$ , $I_{D} = 250 \mu A$	75			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.5		4.5	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 75 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	μA	
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10$ V, $V_{GS} = 10$ V	70			Α	
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0051	0.0062	0	
Drain-Source On-State Resistance <sup>a</sup>	<sup>r</sup> DS(on)	$V_{GS}$ = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.0082	0.0105	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		50		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			4620		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 30 V, f = 1 MHz		517			
Reverse Transfer Capacitance	C <sub>rss</sub>			247			
Total Gate Charge <sup>c</sup>	Qg			75	115	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 30 V, $V_{GS}$ = 10 V, $I_D$ = 50 A		25.5			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			20			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.2	2.4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			16	30		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 0.6 $\Omega$		11	20		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ 50 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 1 $\Omega$		24	40	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			10	20		
Source-Drain Diode Ratings and Cha	aracteristics T	<sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	۱ <sub>S</sub>				85	٨	
Pulsed Current	I <sub>SM</sub>				240	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.83	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			60	100	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 75 A, di/dt = 100 A/μs		3.3	5	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			100	150	nC	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

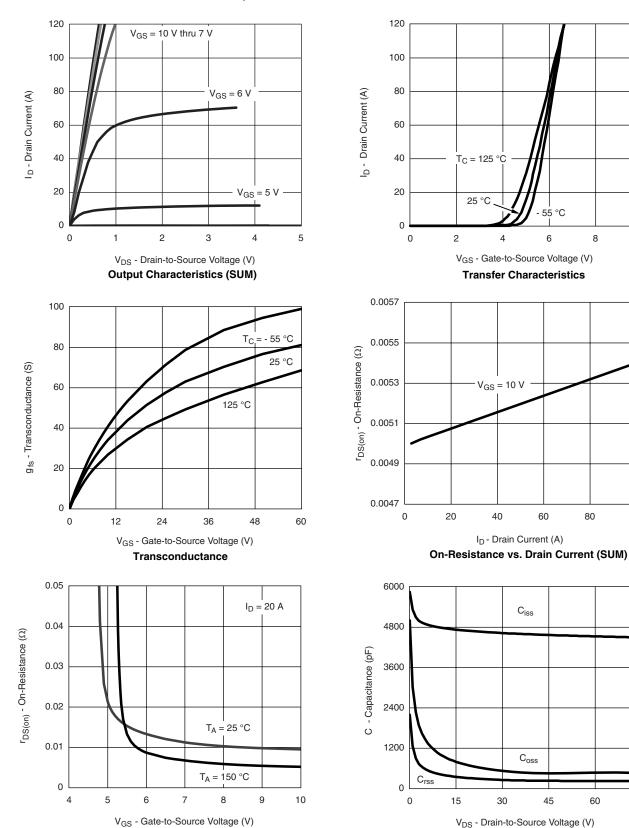
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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100



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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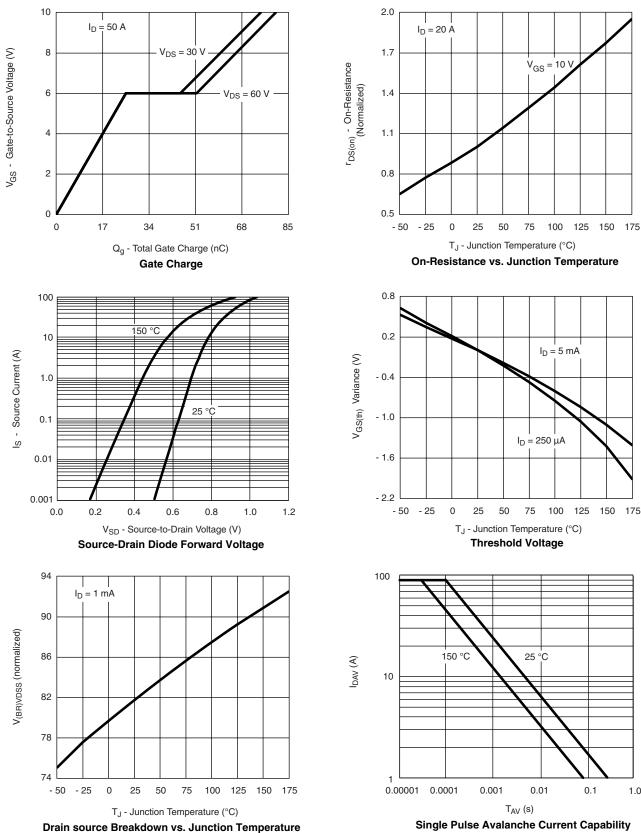
Document Number: 69552 S-72505-Rev. A, 03-Dec-07

On-Resistance vs. Gate-to-Source Voltage (SUM)

Capacitance

75

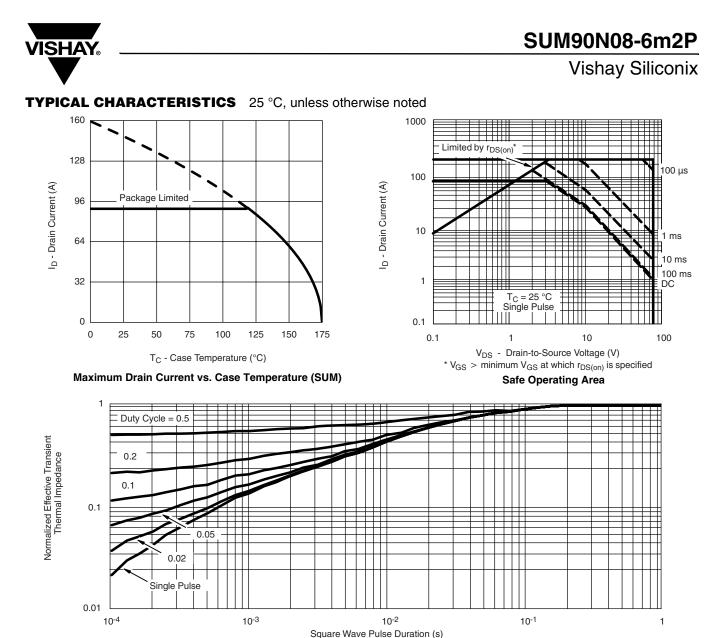
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



vs. Time

1.0





Normalized Thermal Transient Impedance, Junction-to-Case

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TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010 BSC 0.254 B		BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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